

1. Record Nr.	UNINA9911004764603321
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Titolo	Magnetic memory : fundamentals and technology / / Denny D. Tang and Yuan-Jen Lee
Pubbl/distr/stampa	New York, : Cambridge University Press, 2010
ISBN	1-107-20583-2 0-511-84992-3 1-282-53604-4 9786612536045 0-511-67831-2 0-511-68154-2 0-511-67705-7 0-511-68352-9 0-511-68477-0 0-511-67620-4 0-511-67956-4
Descrizione fisica	1 online resource (x, 196 pages) : digital, PDF file(s)
Altri autori (Persone)	LeeYuan-Jen
Disciplina	621.39/73
Soggetti	Magnetic memory (Computers) Computer storage devices
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Title from publisher's bibliographic system (viewed on 05 Oct 2015).
Nota di contenuto	Machine generated contents note: 1. Basic magnetostatics; 2. Magnetic films; 3. Properties of patterned ferromagnetic film; 4. Magnetoresistance effects and memory devices; 5. Field-write mode MRAMs; 6. Spin torque transfer MRAM; 7. Applications of MTJ based technology; Appendices: A. Unit conversion table cgs vs. SI; B. Dimensions of magnetism; C. Physical constants; D. Normal (Gaussian) distribution and quantile plot; E. Weibull distribution; F. TDDB reliability test of thin film; G. Binomial distribution and Poisson distribution; H. Defect density; I. Fe, Co, Ni element chemistry parameters; J. Soft error, hard fail and design margin.
Sommario/riassunto	If you are a semiconductor engineer or a magnetics physicist

developing magnetic memory, get the information you need with this, the first book on magnetic memory. From magnetics to the engineering design of memory, this practical book explains key magnetic properties and how they are related to memory performance, characterization methods of magnetic films, and tunneling magnetoresistance effect devices. It also covers memory cell options, array architecture, circuit models, and read-write engineering issues. You'll understand the soft fail nature of magnetic memory, which is very different from that of semiconductor memory, as well as methods to deal with the issue. You'll also get invaluable problem-solving insights from real-world memory case studies. This is an essential book for semiconductor engineers who need to understand magnetics, and for magnetics physicists who work with MRAM. It is also a valuable reference for graduate students working in electronic/magnetic device research.
